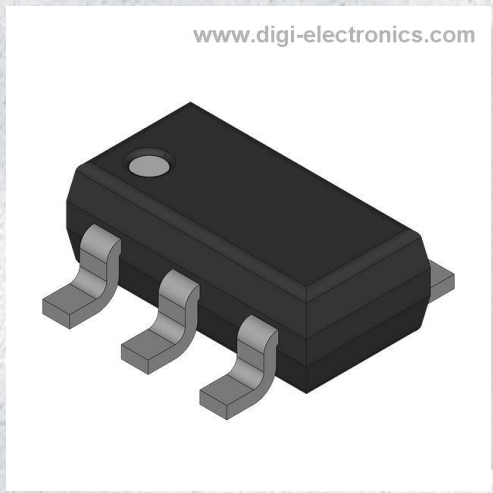
PMN27XPE115 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	PMN27XPE115-DG
Manufacturer	NXP USA Inc.
Manufacturer Product Number	PMN27XPE115
Description	SMALL SIGNAL FET
Detailed Description	P-Channel 20 V 4.4A (Ta) 530mW (Ta), 8.33W (Tc) Surface Mount 6-TSOP

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMN27XPE115	NXP USA Inc.
Series:	Product Status:
-	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	4.4A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
2.5V, 4.5V	30mOhm @ 3A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.25V @ 250µA	22.5 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	1770 pF @ 10 V
FET Feature:	Power Dissipation (Max):
-	530mW (Ta), 8.33W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
6-TSOP	SC-74, SOT-457

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
Not applicable	1 (Unlimited)
REACH Status:	ECCN:
Vendor Undefined	EAR99
HTSUS:	
8541.21.0095	

PMN27XPE

20 V, single P-channel Trench MOSFET

20 September 2012 Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Fast switching
- Trench MOSFET technology
- 2 kV ESD protection

1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

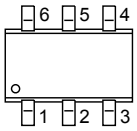
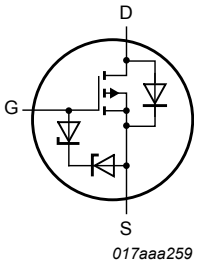
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_{amb} = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-5.7	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3 A; T_j = 25 °C		-	27	30	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

Scan or click this QR code to view the latest information for this product

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	 TSOP6 (SOT457)	
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		
6	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMN27XPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
PMN27XPE	WC

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_{amb} = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I_D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-5.7	A
		V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-4.4	A
		V_{GS} = -4.5 V; T_{amb} = 100 °C	[1]	-	-3.5	A
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; t_p ≤ 10 µs		-	-22	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	530	mW
			[1]	-	1250	mW
		T_{sp} = 25 °C		-	8330	mW

Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	-1.3	A
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[3] Measured between all pins.

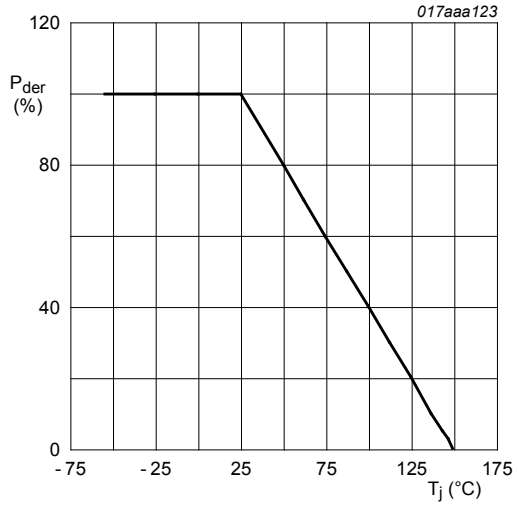


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

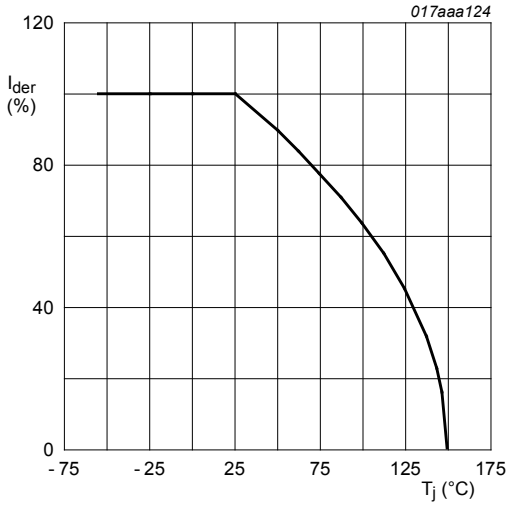
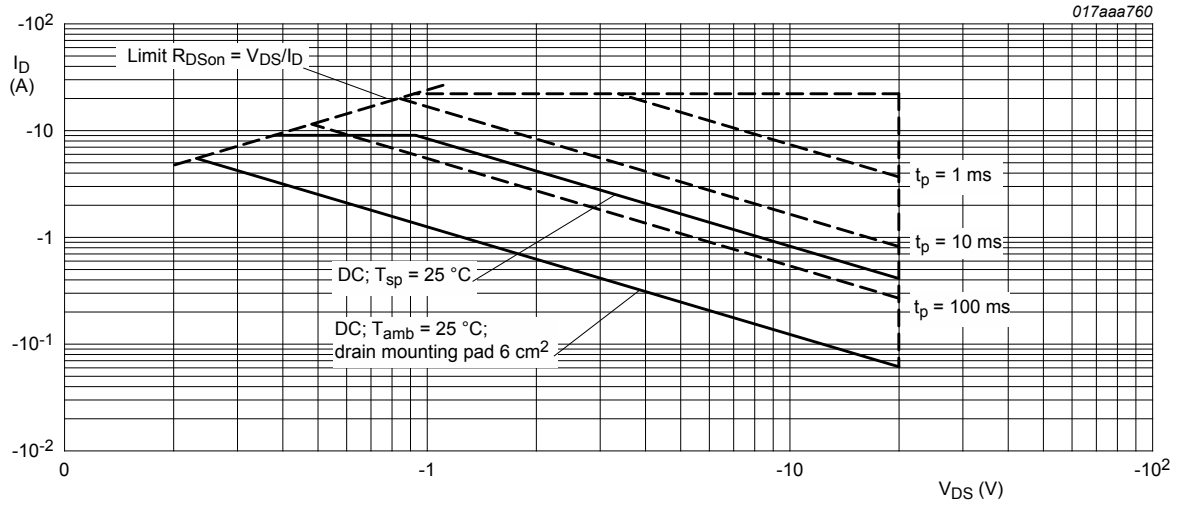


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

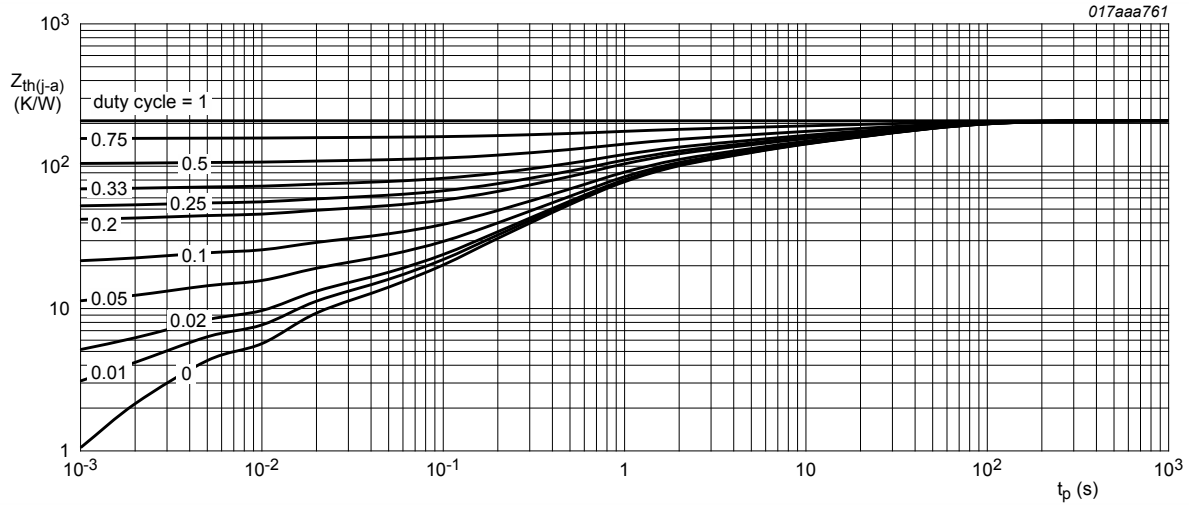
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	206	237	K/W
			[2]	-	86	100	K/W
			[3]	-	52	60	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	13	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint

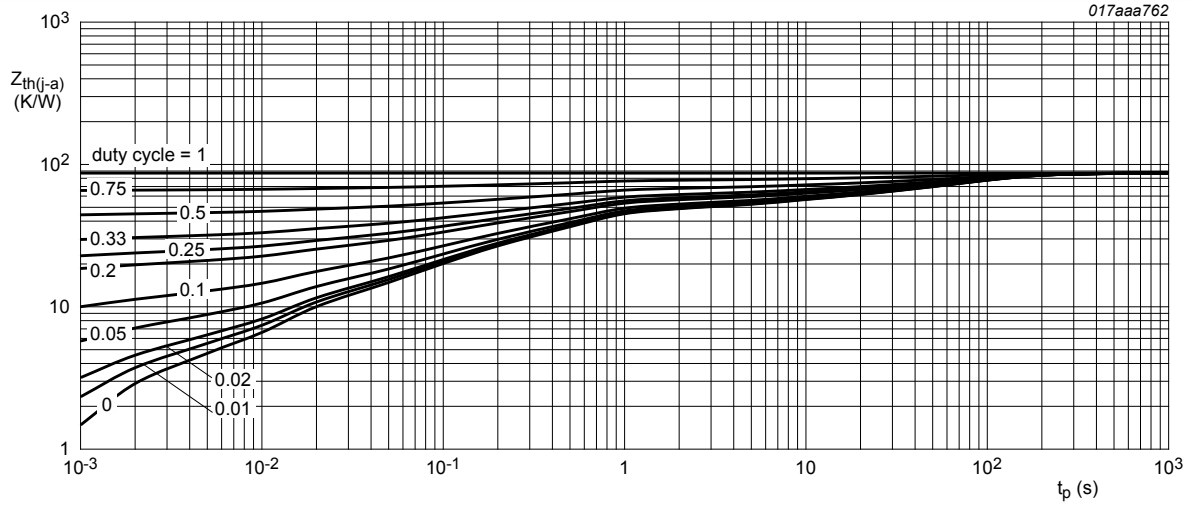
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2, $t \leq 5$ s



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm^2

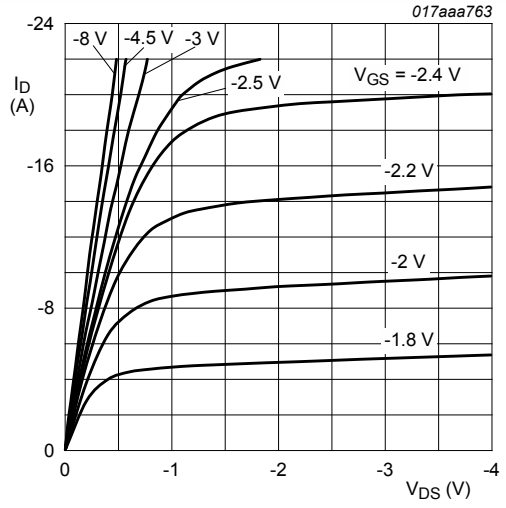
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

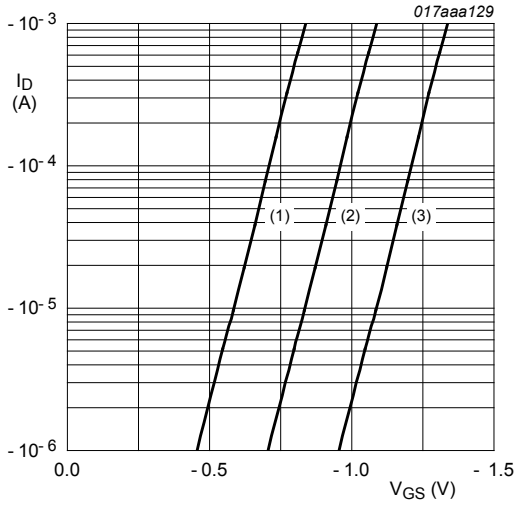
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C		-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS}; T_j = 25 °C		-0.75	-1	-1.25	V
I_{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	µA
I_{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C		-	-	10	µA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-10	µA
R_{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3 A; T_j = 25 °C		-	27	30	mΩ
		V_{GS} = -4.5 V; I_D = -3 A; T_j = 150 °C		-	56	64	mΩ
		V_{GS} = -2.5 V; I_D = -3 A; T_j = 25 °C		-	39	44	mΩ
g_{fs}	forward transconductance	V_{DS} = -10 V; I_D = -3 A; T_j = 25 °C		-	16	-	S
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = -10 V; I_D = -3 A; V_{GS} = -4.5 V; T_j = 25 °C		-	15	22.5	nC
Q_{GS}	gate-source charge			-	3	-	nC
Q_{GD}	gate-drain charge			-	3	-	nC
C_{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	1770	-	pF
C_{oss}	output capacitance			-	254	-	pF
C_{rss}	reverse transfer capacitance			-	180	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = -10 V; I_D = -3 A; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	15	-	ns
t_r	rise time			-	22	-	ns
$t_{d(off)}$	turn-off delay time			-	37	-	ns
t_f	fall time			-	29	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = -1.3 A; V_{GS} = 0 V; T_j = 25 °C		-	-0.7	-1.2	V



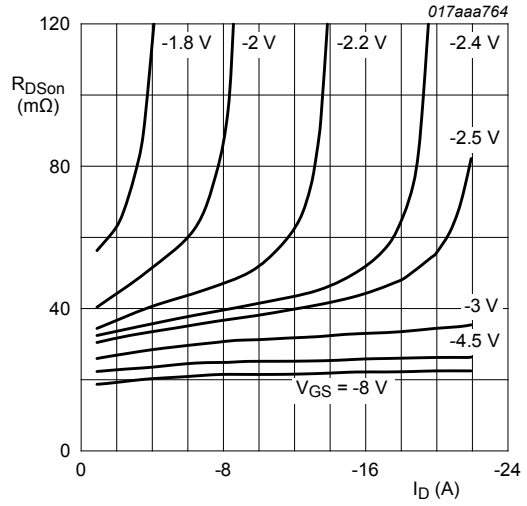
T_j = 25 °C

Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



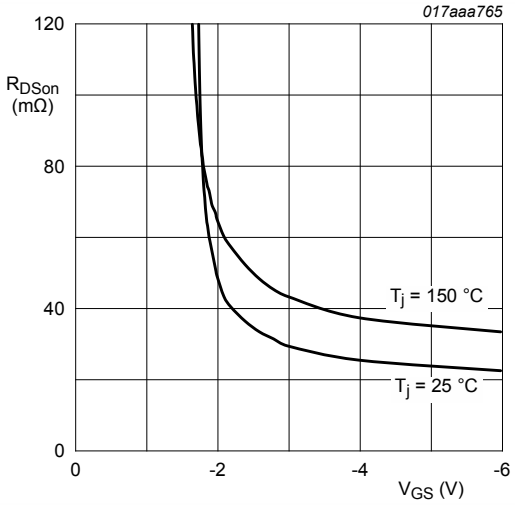
T_j = 25 °C; V_{DS} = -3 V
(1) minimum values
(2) typical values
(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



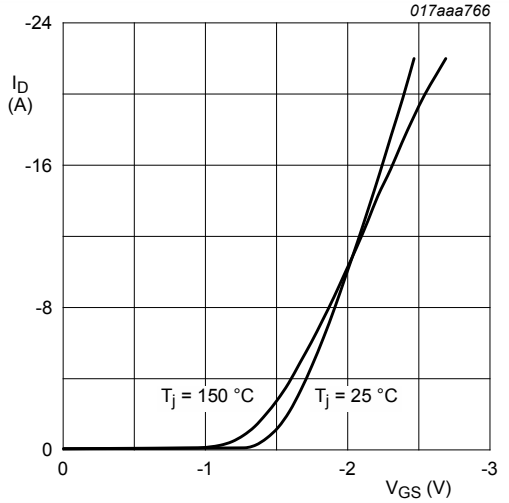
T_j = 25 °C

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



I_D = -3 A

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DSon}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

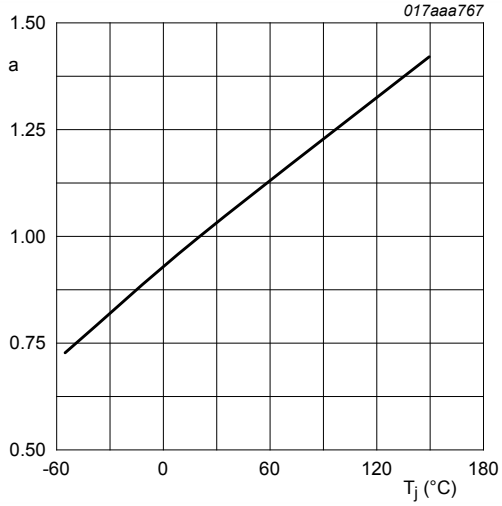
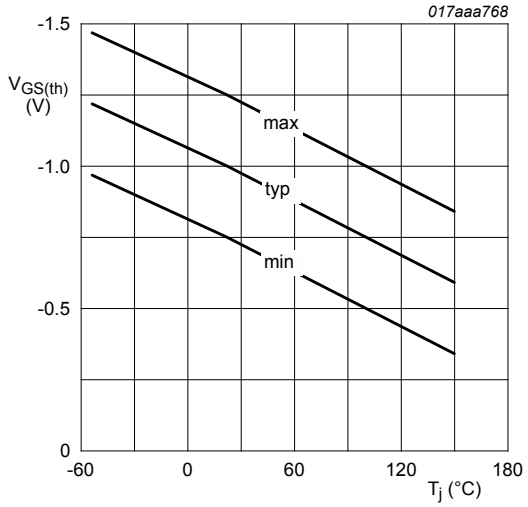


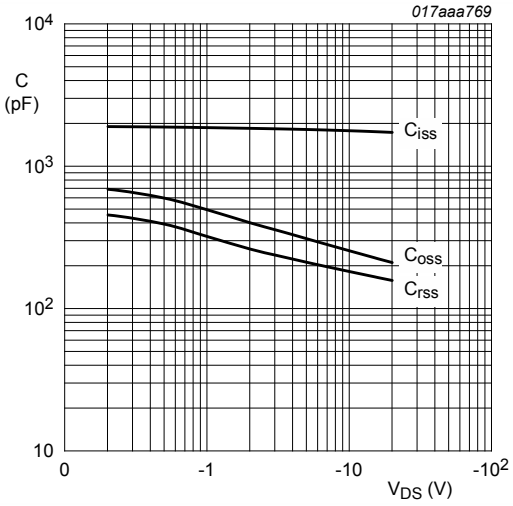
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$



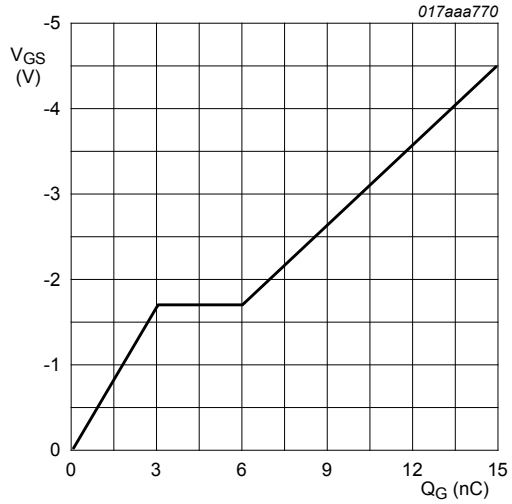
I_D = -0.25 mA; V_{DS} = V_{GS}

Fig. 12. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = -3 A; V_{DS} = -10 V; T_{amb} = 25 °C

Fig. 14. Gate-source voltage as a function of gate charge; typical values

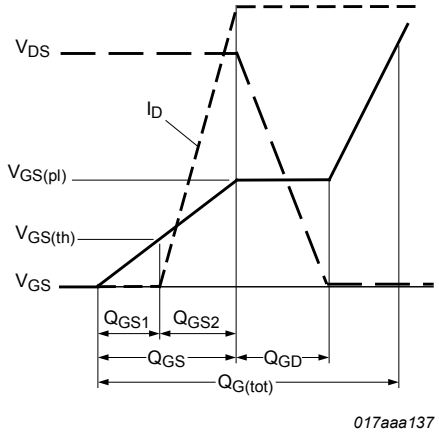
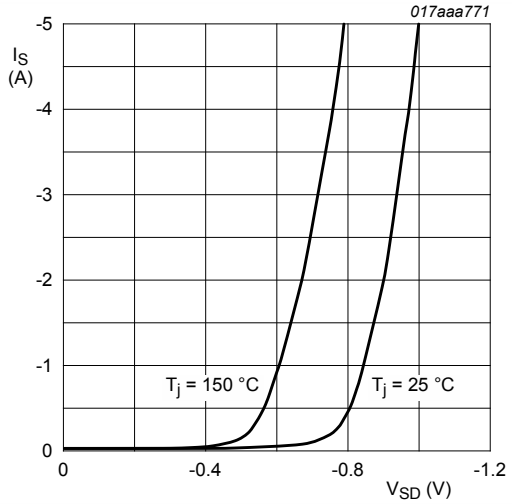


Fig. 15. Gate charge waveform definitions



V_{GS} = 0 V

Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

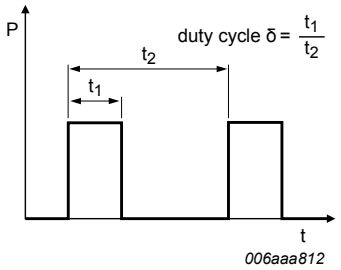


Fig. 17. Duty cycle definition

9. Package outline

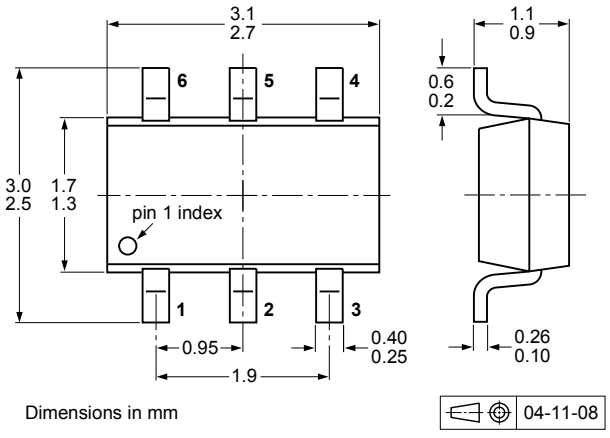


Fig. 18. Package outline TSOP6 (SOT457)

10. Soldering

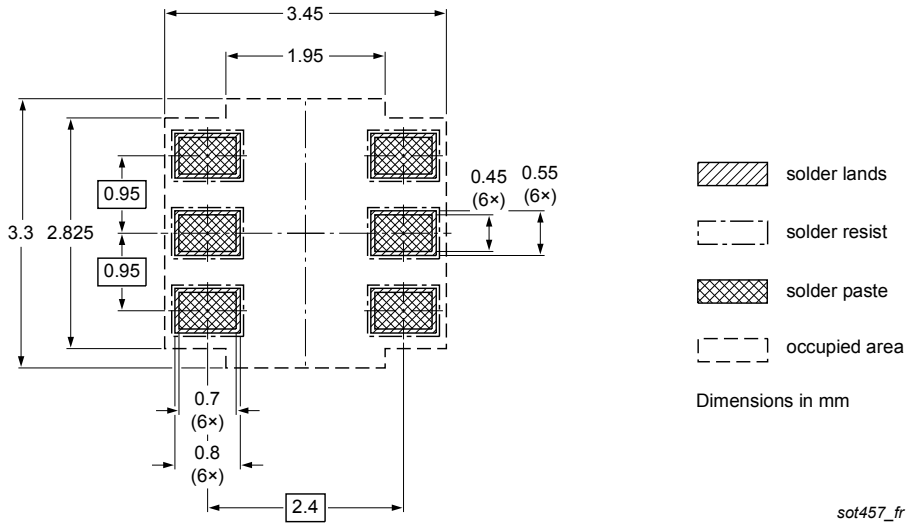


Fig. 19. Reflow soldering footprint for TSOP6 (SOT457)

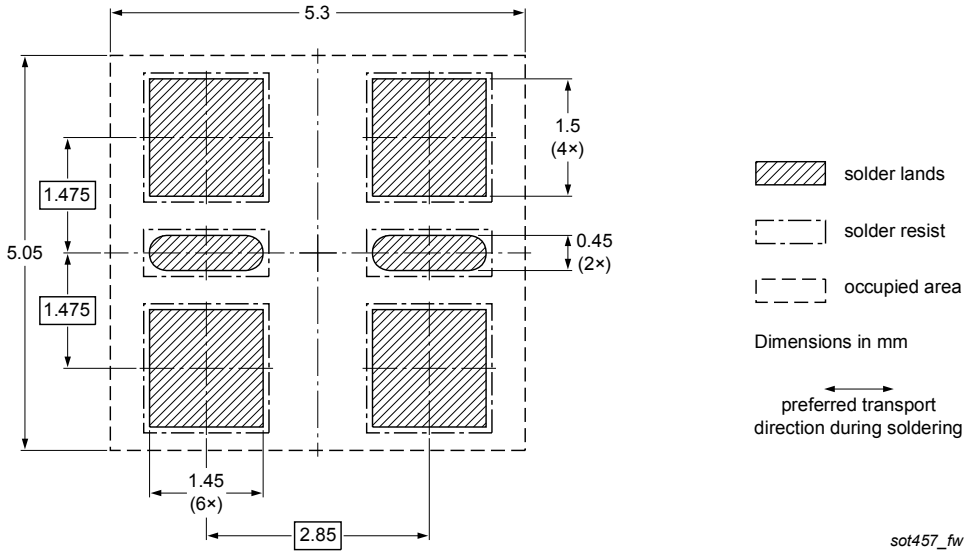


Fig. 20. Wave soldering footprint for TSOP6 (SOT457)

11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN27XPE v.1	20120920	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

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